



#### 30V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage 30 V Current 0.6A

#### **Features**

- RDS(ON), VGS@4,5V, ID@0.6A<220mΩ</li>
- RDS(ON) , VGS@2.5V, ID@0.4A<290mΩ</li>
- RDS(ON), VGS@1.8V, ID@0.1A<600mΩ
- Advanced Trench Process Technology
- Specially Designed for Load Switch or PWM application.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

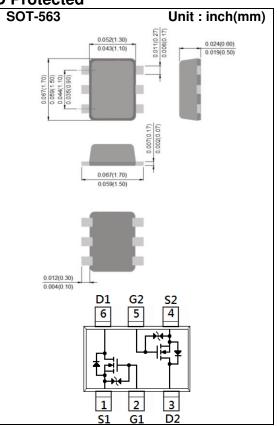
#### **Mechanical Data**

• Case: SOT-563 Package

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0026 grams

Marking: X04



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 8	V
Continuous Drain Current		ID	0.6	Α
Pulsed Drain Current		I <sub>DM</sub>	2.4	Α
Power Dissipation	T <sub>a</sub> =25°C	PD	300	mW
	Derate above 25°C		2.4	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance				
- Junction to Ambient <sup>(Note 3)</sup>		$R_{ heta JA}$	417	°C/W





### **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
Gate Threshold Voltage	$V_{\text{GS(th)}}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5	0.79	1.3	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.6A	-	177	220	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =0.4A	-	223	290	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =0.1A	-	330	600	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	0.01	1	uA
Gate-Source Leakage Current	Igss	V <sub>GS=<u>+</u>8V, V<sub>DS</sub>=0V</sub>	-	<u>+</u> 1.5	<u>+</u> 10	uA
Dynamic <sup>(Note 5)</sup>						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =15V, I <sub>D</sub> =0.6A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	1.5	-	nC
Gate-Source Charge	$Q_gs$		-	0.3	-	
Gate-Drain Charge	$Q_gd$		-	0.3	-	
Input Capacitance	Ciss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	93	-	pF
Output Capacitance	Coss		-	19	-	
Reverse Transfer Capacitance	Crss		-	6	-	
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =0.6A, V <sub>GS</sub> =4.5V,	-	6	-	
Turn-On Rise Time	tr		-	33	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	37	-	
Turn-Off Fall Time	tf	$R_G=6\Omega^{(Note\ 1,2)}$	-	32	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	,				0.4	А
Diode Forward Current	ls		-	-	0.4	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.81	1.2	V

#### NOTES:

- 1. Pulse width < 300us, Duty cycle < 2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

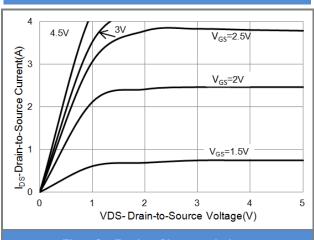


Fig.1 On-Region Characteristics

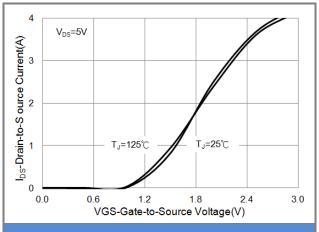


Fig.2 Transfer Characteristics

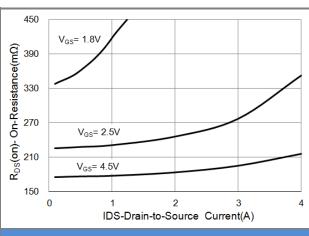


Fig.3 On-Resistance vs. Drain Current

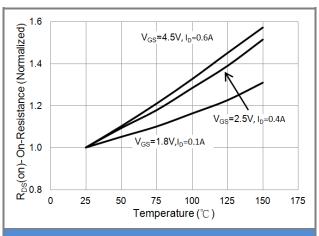
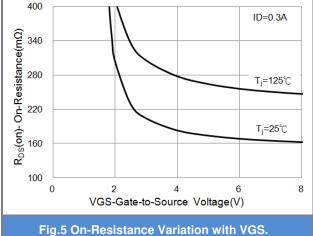
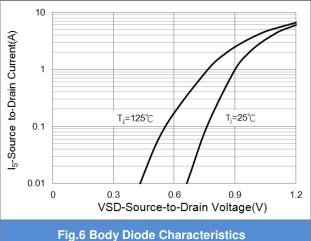


Fig.4 On-Resistance vs. Junction temperature









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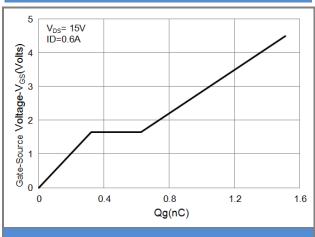


Fig.7 Gate-Charge Characteristics

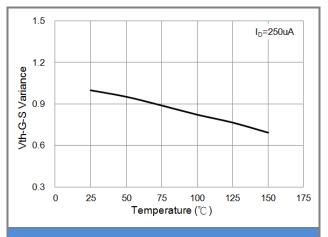


Fig.8 Threshold Voltage Variation with Temperature

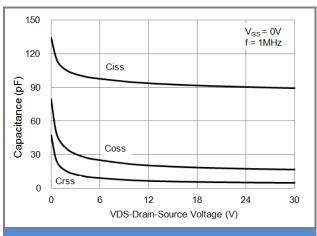


Fig.9 Capacitance vs. Drain-Source Voltage

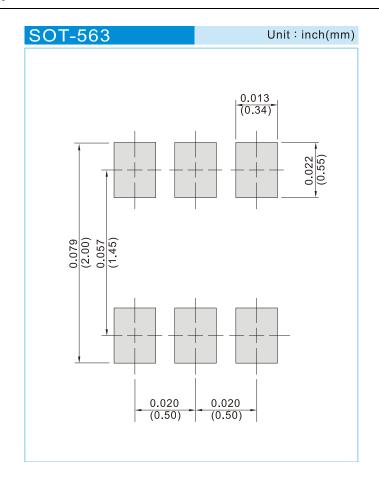




# Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJX8804_R1_00002	SOT-563	4K pcs / 7" reel	X04	Halogen free RoHS compliant
PJX8804_R2_00002	SOT-563	10K pcs / 13" reel	X04	Halogen free RoHS compliant

## **Mounting Pad Layout**







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